



100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | Max R _{DS(ON)} | Max I _D T _A = +25°C (Note 7) |
|----------------------|------------------------------|--|
| 100V | 250mΩ @ $V_{GS} = 10V$ | 1.9A |
| 100 V | 300mΩ @ V _{GS} = 6V | 1.68A |

Description and Applications

This new generation MOSFET features a unique structure, combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency power management applications such as:

- DC DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Available (Note 4)

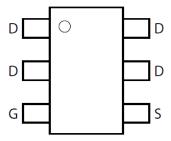
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.015 grams (Approximate)

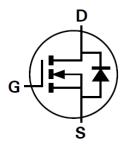
SOT26







Pinout Top-View



Device Symbol

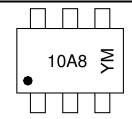
Ordering Information (Note 4 & 5)

| Part Number | Compliance | Case | Packing |
|----------------|------------|-------|---------|
| ZXMN10A08E6QTA | Automotive | SOT26 | 3,000 |
| ZXMN10A08E6QTC | Automotive | SOT26 | 10,000 |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



10A8 = Product Type Marking Code YM = Date Code Marking

Y or \overline{Y} = Year (ex: C = 2015)

M or \overline{M} = Month (ex: 9 = September)

Date Code Key

| Year | 2015 | ; ; | 2016 | 2017 | 2018 | 2019 | 2020 | 202 | 1 20 | 22 2 | 2023 | 2024 | 2025 |
|-------|------|-----|------|------|------|------|------|-----|------|------|------|------|------|
| Code | С | | D | Е | F | G | Н | I | , | J | K | L | М |
| Month | h | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code |) | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|--|----------------|---|------------------|-------|------|
| Drain-Source Voltage | | | V _{DSS} | 100 | V |
| Gate-Source Voltage | | | V _{GS} | ±20 | V |
| Continuous Drain Current | | (Note 7) | - I _D | 1.9 | |
| | 101/ | $T_A = +70 ^{\circ}\text{C} \text{ (Note 7)}$ | | 1.5 | Α |
| | $V_{GS} = 10V$ | (Note 6) | | 1.5 | A |
| | | (Note 9) | | 3.5 | |
| Pulsed Drain Current | | (Note 8) | I _{DM} | 8.6 | Α |
| Continuous Source Current (Body Diode) (Note | | (Note 7) | I _S | 2.5 | Α |
| Pulsed Source Current (Body Diode) (Note 8) | | (Note 8) | I _{SM} | 8.6 | Α |

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

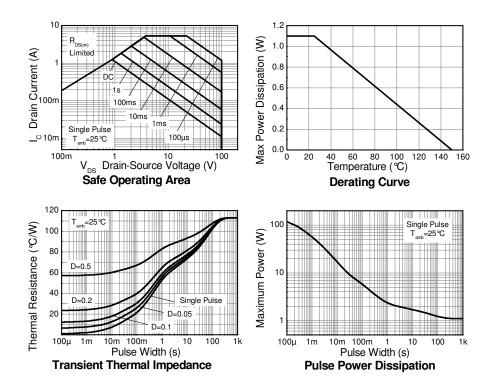
| Characteristic | | Symbol | Value | Unit | |
|--|----------|-----------------------------------|-------------|------|--|
| | (Note 6) | | 1.1 | W | |
| Power Dissipation | (Note 7) | P_{D} | 1.7 | | |
| | (Note 9) | | 6.3 | | |
| The word Decistance I westing to Ambient | (Note 6) | 6 | 114 | °C/W | |
| Thermal Resistance, Junction to Ambient | (Note 7) | R_{\thetaJA} | 73.5 | | |
| Thermal Resistance, Junction to Leads | (Note 9) | $R_{	heta JL}$ | 19.7 | °C/W | |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +150 | °C | |

Notes:

- 6. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions 7. For a device surface mounted on FR4 PCB measured at t ≤ 5 secs.

 8. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300µs pulse width limited by maximum junction temperature.
- 9. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics





Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

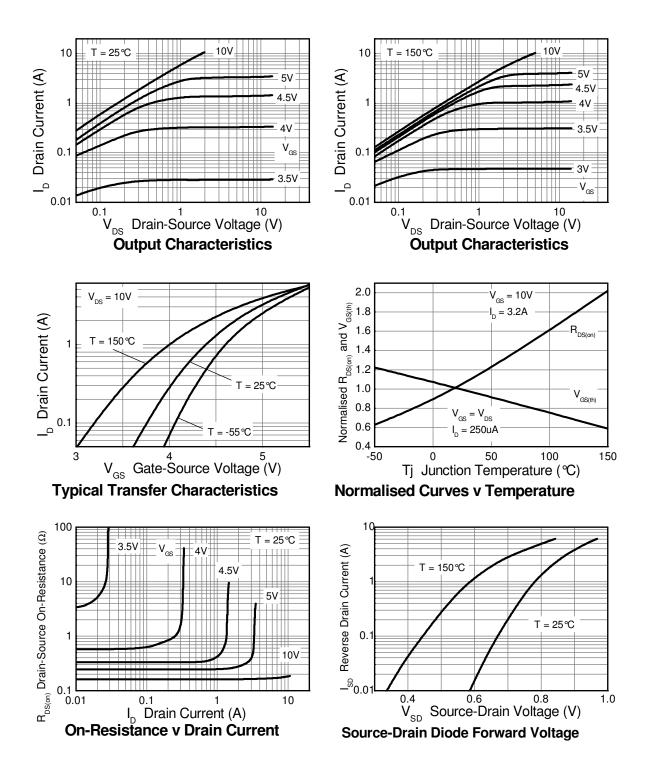
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|---|----------------------|-----|------|------|------|---|--|
| OFF CHARACTERISTICS | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 100 | _ | _ | V | $I_D = 250 \mu A, V_{GS} = 0 V$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 0.5 | μΑ | V _{DS} = 100V, V _{GS} = 0V | |
| Gate-Source Leakage | I _{GSS} | _ | _ | 100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 2.0 | | 4.0 | V | $I_D = 250\mu A$, $V_{DS} = V_{GS}$ | |
| Static Drain Source On Registance (Note 10) | D | | | 0.25 | | $V_{GS} = 10V, I_D = 3.2A$ | |
| Static Drain-Source On-Resistance (Note 10) | R _{DS} (ON) | | _ | 0.30 | Ω | $V_{GS} = 6V, I_D = 2.6A$ | |
| Forward Transconductance (Notes 10 & 12) | g fs | _ | 5.0 | _ | S | $V_{DS} = 15V, I_D = 3.2A$ | |
| Diode Forward Voltage (Note 10) | V_{SD} | _ | 0.87 | 0.95 | V | I _S = 3.2A, V _{GS} = 0V | |
| Reverse Recovery Time (Note 12) | t _{rr} | | 27 | _ | ns | 1 01 11/11 1001/ | |
| Reverse Recovery Charge (Note 12) | Qrr | _ | 32 | _ | nC | I _S = 1.2A, di/dt = 100A/μs | |
| DYNAMIC CHARACTERISTICS (Note 12) | | | | | | | |
| Input Capacitance | Ciss | _ | 405 | _ | pF | | |
| Output Capacitance | Coss | _ | 28.2 | _ | pF | $V_{DS} = 50V, V_{GS} = 0V$ f = 1MHz | |
| Reverse Transfer Capacitance | C _{rss} | _ | 14.2 | _ | pF | -1 = 11VII 12 | |
| Gate Charge (Note 11) | Qg | _ | 4.2 | _ | nC | $V_{GS} = 5V, V_{DS} = 50V$ $I_{D} = 1.2A$ | |
| Total Gate Charge (Note 11) | Qg | _ | 7.7 | _ | nC | | |
| Gate-Source Charge (Note 11) | Q _{gs} | _ | 1.8 | _ | nC | $V_{GS} = 10V, V_{DS} = 50V$ | |
| Gate-Drain Charge (Note 11) | Q _{gd} | _ | 2.1 | _ | nC | $I_D = 1.2A$ | |
| Turn-On Delay Time (Note 11) | t _{d(on)} | _ | 3.4 | _ | ns | | |
| Turn-On Rise Time (Note 11) | t _r | _ | 2.2 | _ | ns | V _{DD} = 30V, V _{GS} = 10V | |
| Turn-Off Delay Time (Note 11) | t _{d(off)} | _ | 8 | _ | ns | $I_D = 1.2A, R_G \cong 6.0\Omega$ | |
| Turn-Off Fall Time (Note 11) | t _f | | 3.2 | | ns | | |

Notes:

^{10.} Measured under pulsed conditions. Width \leq 300 μ s. Duty cycle \leq 2%. 11. Switching characteristics are independent of operating junction temperature. 12. For design aid only, not subject to production testing.

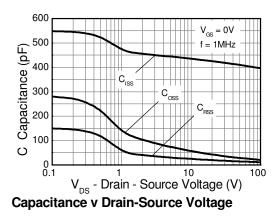


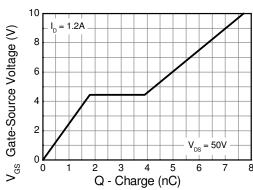
Typical Characteristics





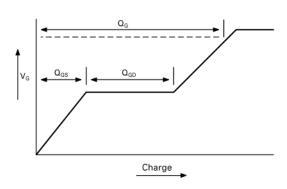
Typical Characteristics (continued)





Gate-Source Voltage v Gate Charge

Test Circuits



regulator

12V 0.2μF 50k Same as D.U.T

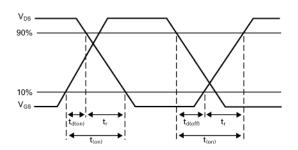
V_{GS}

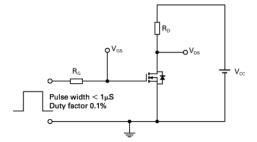
D.U.T

Current

Basic gate charge waveform

Gate charge test circuit





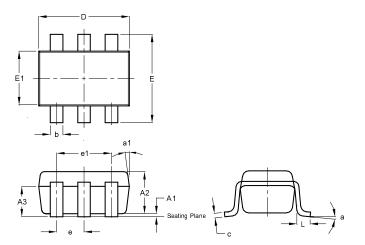
Switching time waveforms

Switching time test circuit



Package Outline Dimensions

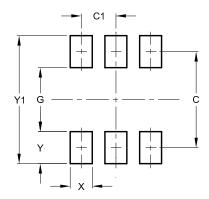
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| | SOT26 | | | | | | | |
|-----|-------|-------|-------|--|--|--|--|--|
| Dim | Min | Max | Тур | | | | | |
| A1 | 0.013 | 0.10 | 0.05 | | | | | |
| A2 | 1.00 | 1.30 | 1.10 | | | | | |
| A3 | 0.70 | 0.80 | 0.75 | | | | | |
| b | 0.35 | 0.50 | 0.38 | | | | | |
| С | 0.10 | 0.20 | 0.15 | | | | | |
| D | 2.90 | 3.10 | 3.00 | | | | | |
| е | - | 1 | 0.95 | | | | | |
| e1 | - | - | 1.90 | | | | | |
| Е | 2.70 | 3.00 | 2.80 | | | | | |
| E1 | 1.50 | 1.70 | 1.60 | | | | | |
| L | 0.35 | 0.55 | 0.40 | | | | | |
| а | - | - | 8° | | | | | |
| a1 | - | - | 7° | | | | | |
| All | Dimen | sions | in mm | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 2.40 |
| C1 | 0.95 |
| G | 1.60 |
| Х | 0.55 |
| Υ | 0.80 |
| Y1 | 3.20 |

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